

1700V N-Channel Silicon Carbide Power MOSFET

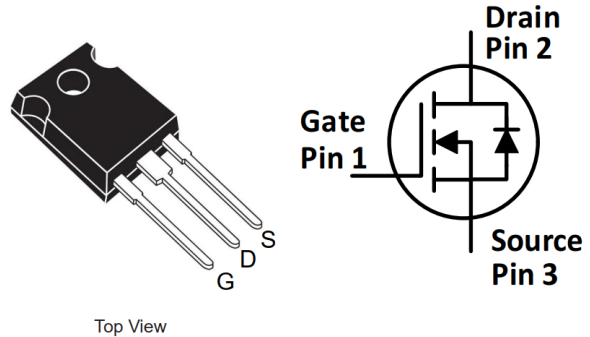
Features:

- Low on-resistance
- Fast switching speed with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{RR})
- Halogen-free, RoHS compliant

Applications:

- Motor drives
- DC/DC converters
- Switched mode power supplies
- Solar inverters

Package:



Part Number	Package
DTN055N170SC3	TO247-3

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions
V_{DS}	Drain-Source voltage	1700	V	$V_{GS}=0\text{V}$, $I_D=100\mu\text{A}$
V_{GS}	Gate-Source voltage	-10 to 22	V	Recommended maximum
I_D	Drain current (continuous)	5.5	A	$T_c=25^\circ\text{C}$
		4	A	$T_c=100^\circ\text{C}$
I_{DM}	Drain current (pulsed)	11	A	Pulse width limited by SOA
P_{TOT}	Total power dissipation	100	W	$T_c=25^\circ\text{C}$
T_{stg}	Storage temperature range	-55 to 175	$^\circ\text{C}$	
T_J	Operating junction temperature	-55 to 175	$^\circ\text{C}$	
T_L	Solder Temperature	260	$^\circ\text{C}$	

Thermal Data

Symbol	Parameter	Value	Unit
$R_{\theta(j-c)}$	Thermal Resistance from Junction to Case	1.5	$^\circ\text{C/W}$

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
I_{DSS}	Zero gate voltage drain current		5	50	μA	$V_{DS}=1700\text{V}, V_{GS}=0\text{V}$
I_{GSS}	Gate leakage current		1	± 100	nA	$V_{DS}=0\text{V}, V_{GS}=-10\sim 22\text{V}$
V_{TH}	Gate threshold voltage		3.2		V	$V_{GS}=V_{DS}, I_D=0.7\text{mA}$
			2			$V_{GS}=V_{DS}, I_D=0.7\text{mA}$ @ $T_c=175^\circ\text{C}$
R_{ON}	Static drain-source on-resistance		1000	1500	$\text{m}\Omega$	$V_{GS}=18\text{V}, I_D=2\text{A}$ @ $T_j=25^\circ\text{C}$
			2100		$\text{m}\Omega$	$V_{GS}=18\text{V}, I_D=2\text{A}$ @ $T_j=175^\circ\text{C}$
C_{iss}	Input capacitance		184		pF	$V_{DS}=1000\text{V}, V_{GS}=0\text{V},$ $f=100\text{kHz}, V_{AC}=25\text{mV}$
C_{oss}	Output capacitance		12		pF	
C_{rss}	Reverse transfer capacitance		3		pF	
E_{oss}	C_{oss} stored energy		7		μJ	
Q_g	Total gate charge		16.5		nC	$V_{DS}=1200\text{V}, I_D=1\text{A},$ $V_{GS}=-6\text{ to }18\text{V}$
Q_{gs}	Gate-source charge		2.5		nC	
Q_{gd}	Gate-drain charge		12		nC	
R_g	Gate input resistance		8.7		Ω	$f=1\text{MHz}$
E_{ON}	Turn-on switching energy		45		μJ	$V_{DS}=1200\text{V}, I_D=2\text{A},$ $V_{GS}=-6\text{ to }18\text{V},$ $R_{G(\text{ext})}=2.5\Omega,$ $L=1000\mu\text{H}$
E_{OFF}	Turn-off switching energy		21		μJ	
$t_{d(\text{on})}$	Turn-on delay time		5		ns	
t_r	Rise time		8			
$t_{d(\text{off})}$	Turn-off delay time		6			
t_f	Fall time		41			

Reverse Diode Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
V_{SD}	Diode forward voltage		3.8		V	$I_{SD}=1\text{A}, V_{GS}=-4\text{V}$
			3.5		V	$I_{SD}=1\text{A}, V_{GS}=-4\text{V}, T_J=175^\circ\text{C}$
t_{rr}	Reverse recovery time		15		ns	$V_{GS}=-4\text{V}$
Q_{rr}	Reverse recovery charge		68		nC	$I_{SD}=2\text{A}, V_R=1200\text{V}, di/dt=2350\text{A}/\mu\text{s}$
I_{RRM}	Peak reverse recovery current		5		A	$T_J=175^\circ\text{C}$

Typical Performance (curves)

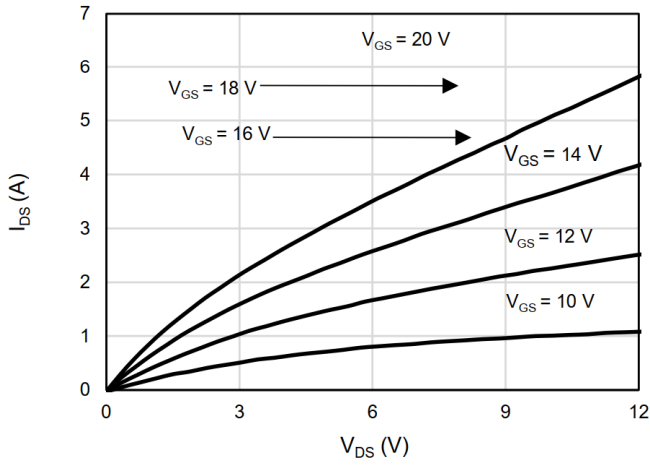


Figure 1: Output Characteristics $T_J = -40^\circ\text{C}$

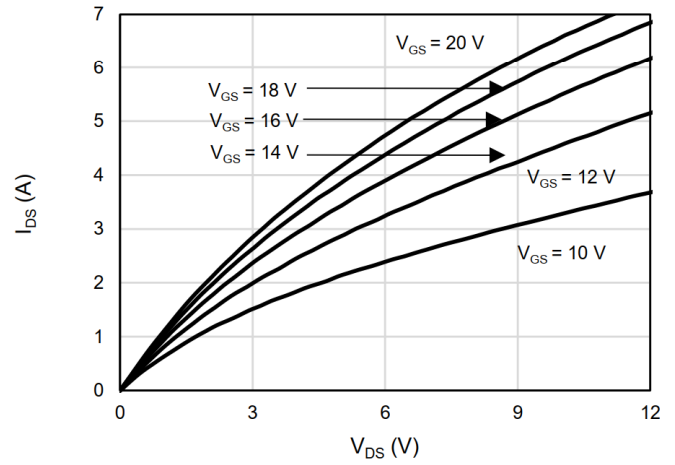


Figure 2: Output Characteristics $T_J = 25^\circ\text{C}$

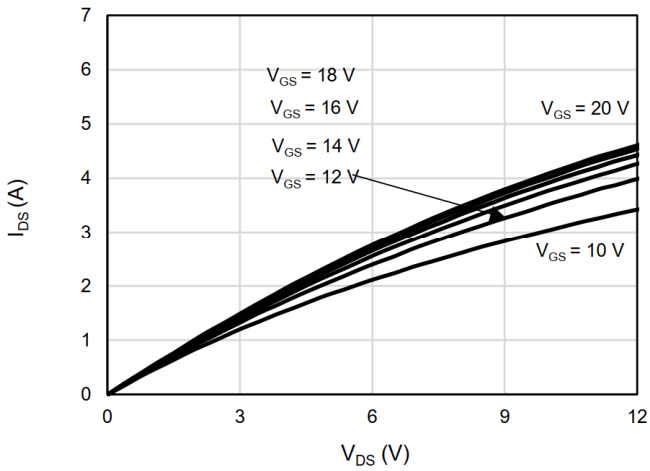


Figure 3: Output Characteristics $T_J = 175^\circ\text{C}$

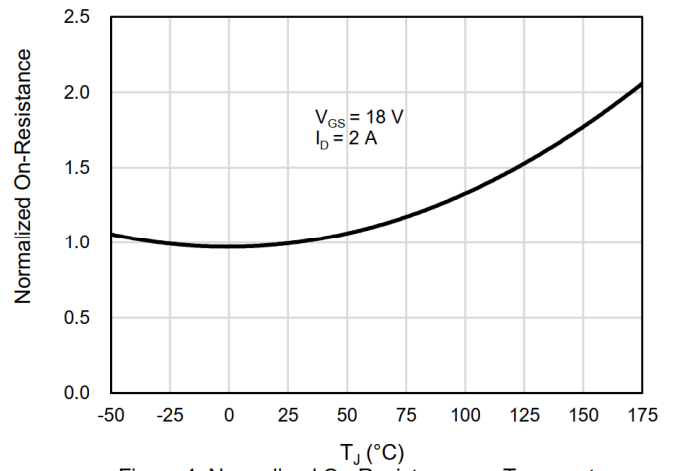


Figure 4: Normalized On-Resistance vs. Temperature

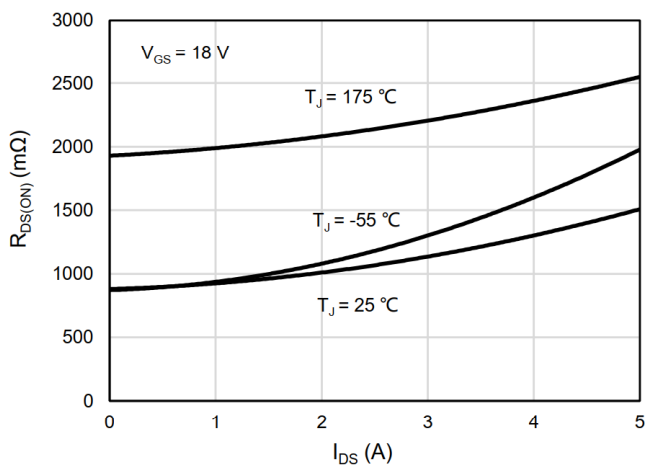


Figure 5: On-Resistance vs. Drain Current For Various Temperatures

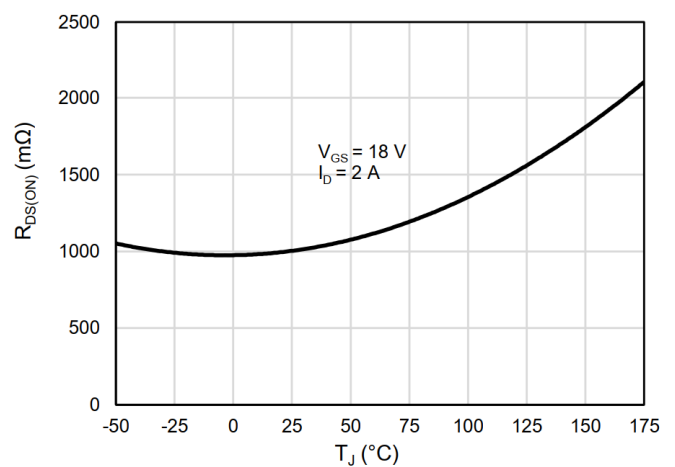


Figure 6: On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance (curves)

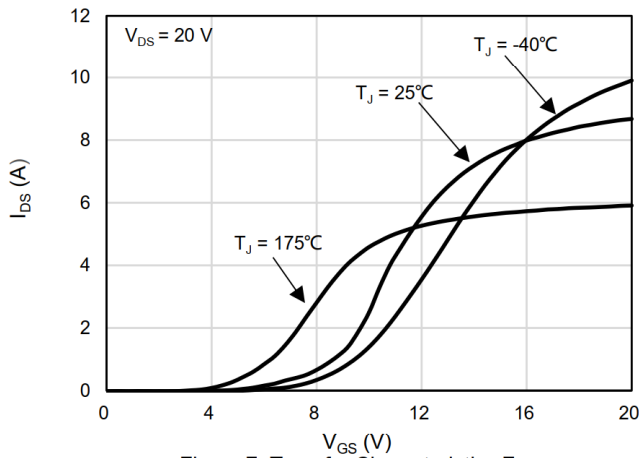


Figure 7: Transfer Characteristics For Various Junction Temperature

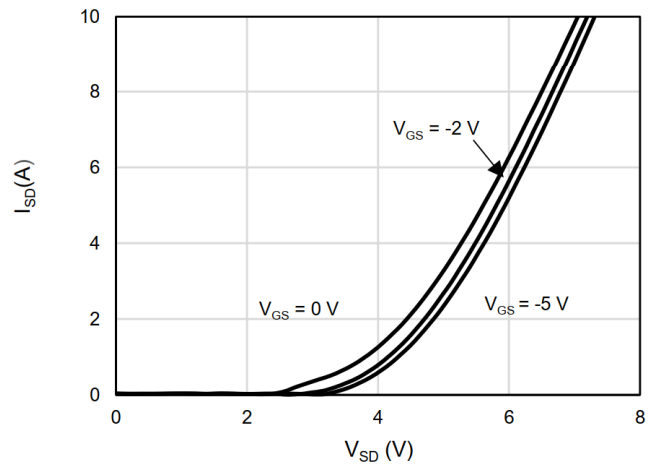


Figure 8: Body Diode Characteristics at -55°C

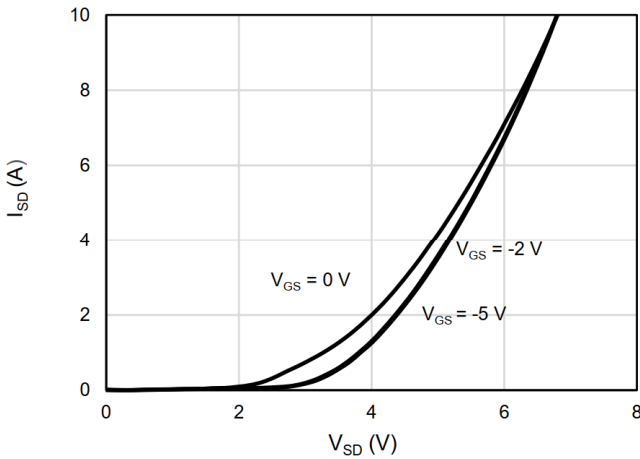


Figure 9: Body Diode Characteristics at 25°C

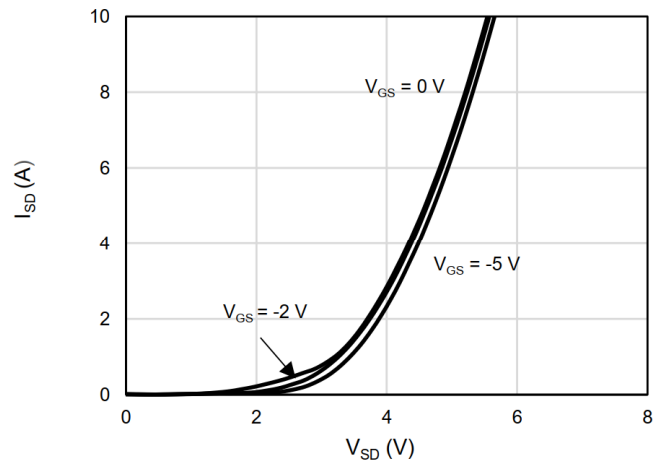


Figure 10: Body Diode Characteristics at 175°C

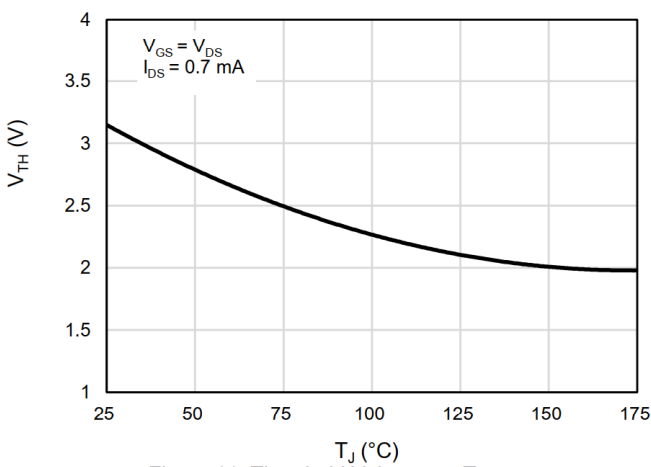


Figure 11: Threshold Voltage vs. Temperature

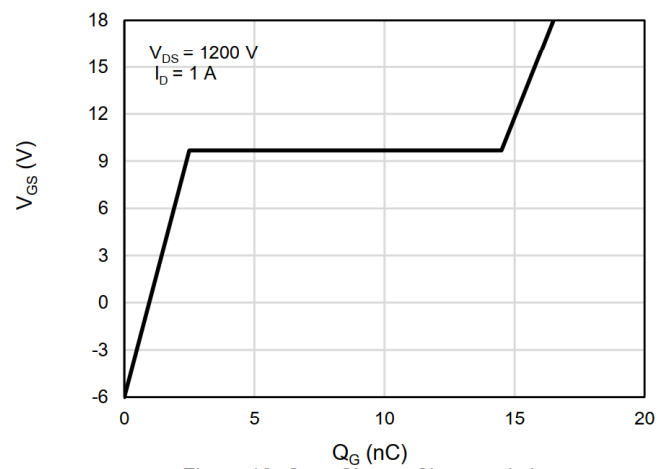


Figure 12: Gate-Charge Characteristics

Typical Performance (curves)

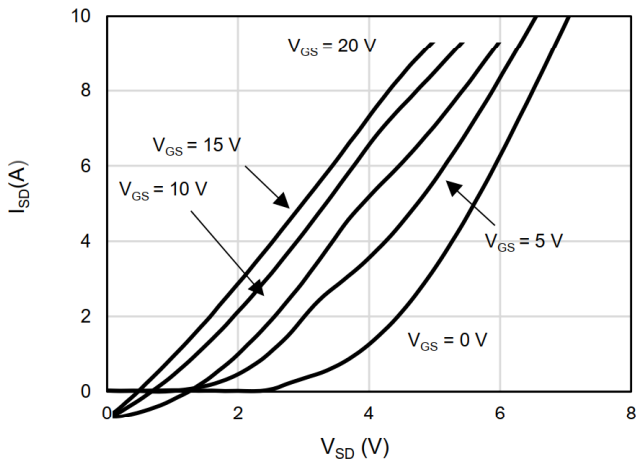


Figure 13: 3rd Quadrant Characteristics at -55°C

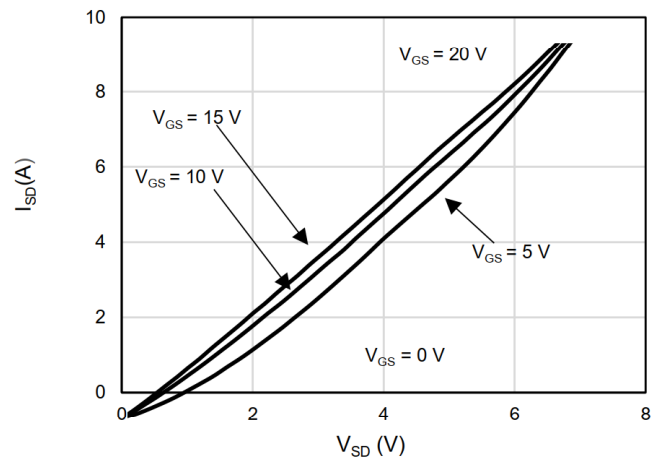


Figure 14: 3rd Quadrant Characteristics at 25°C

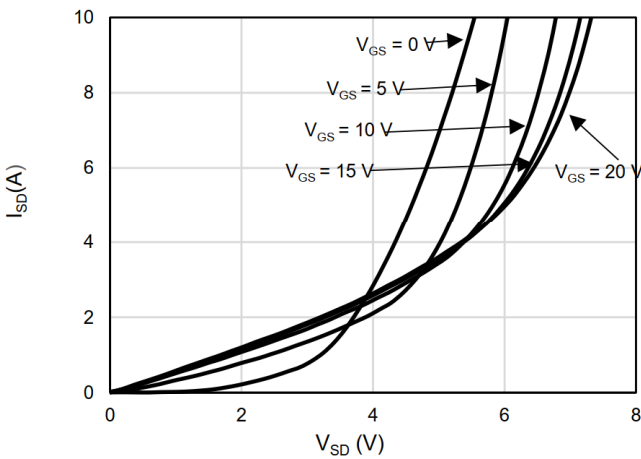


Figure 15: 3rd Quadrant Characteristics at 175°C

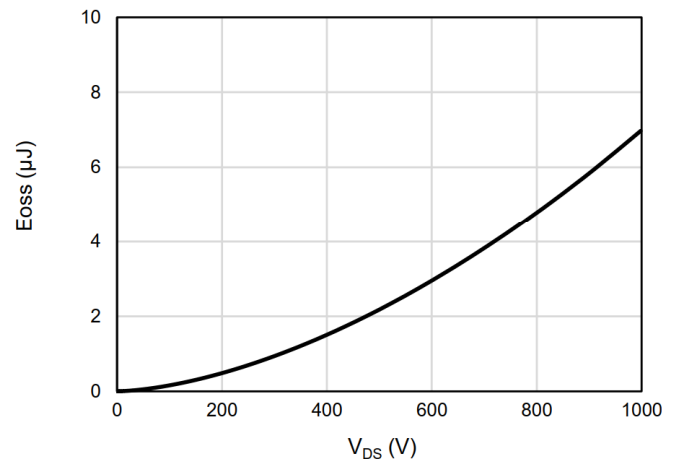


Figure 16: Output Capacitor Stored Energy

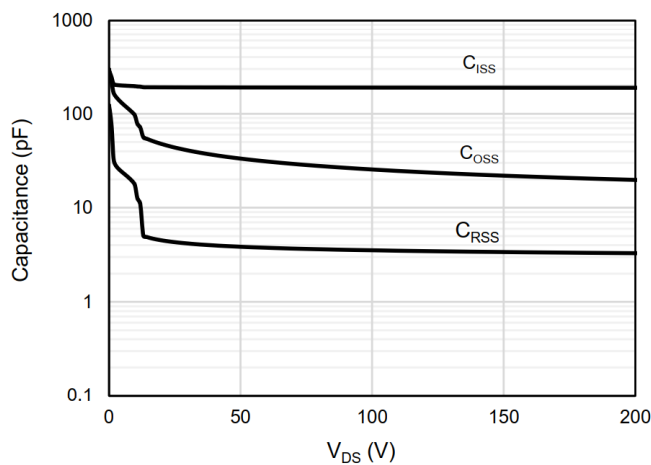


Figure 17: Capacitance Characteristics (0 - 200V)

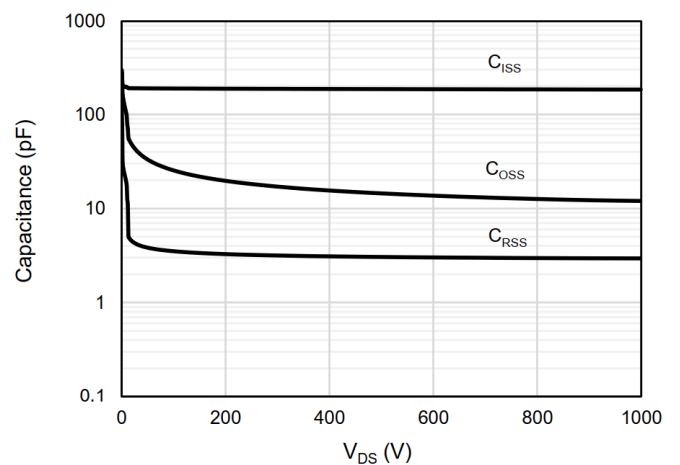


Figure 18: Capacitance Characteristics (0-1000V)

Typical Performance (curves)

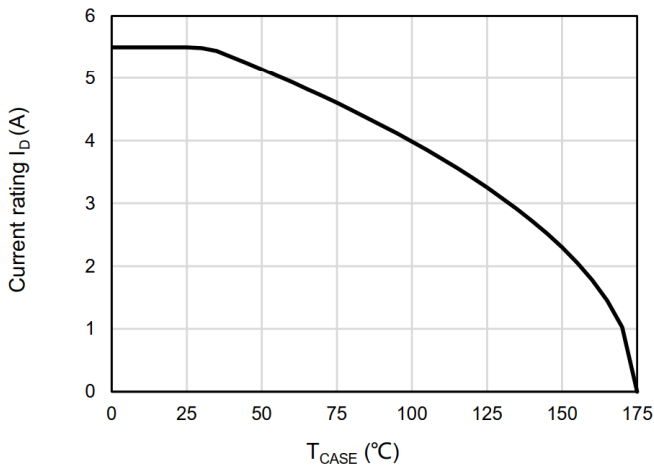


Figure 19: Current De-rating

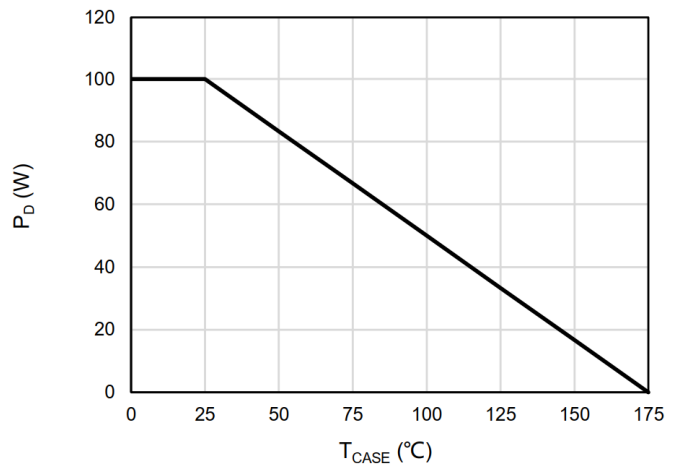


Figure 20: Maximum Power Dissipation Derating vs Case Temperature

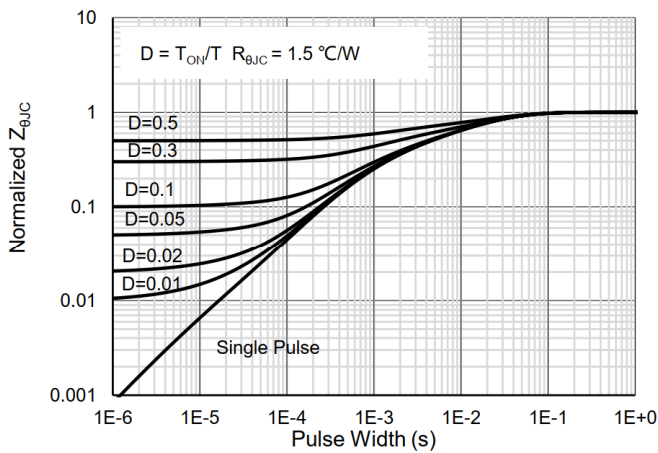


Figure 21: Normalized Maximum Transient Thermal Impedance

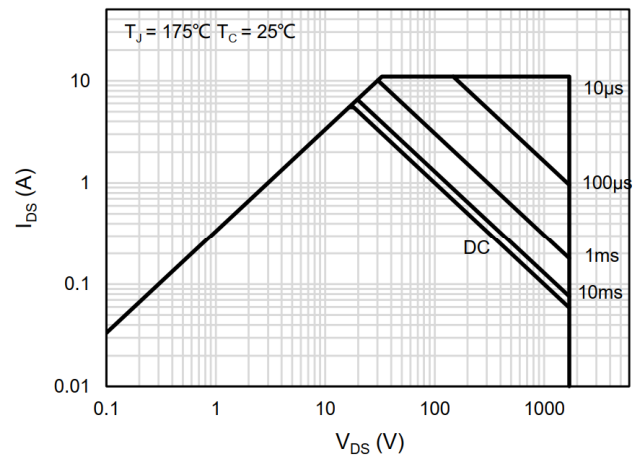


Figure 22: Maximum Forward Biased Safe Operating Area

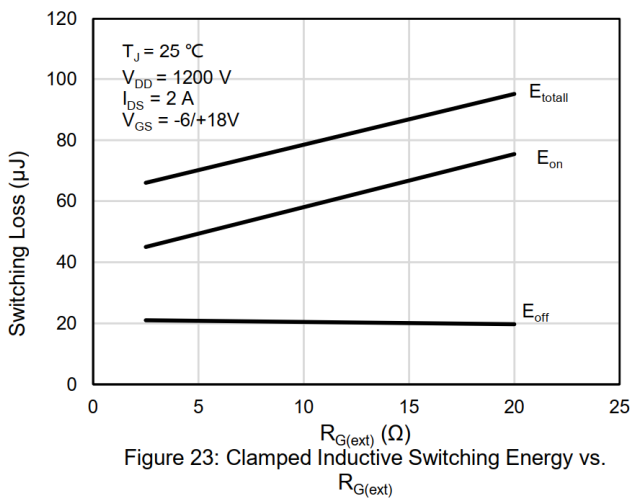


Figure 23: Clamped Inductive Switching Energy vs. $R_{G(ext)}$

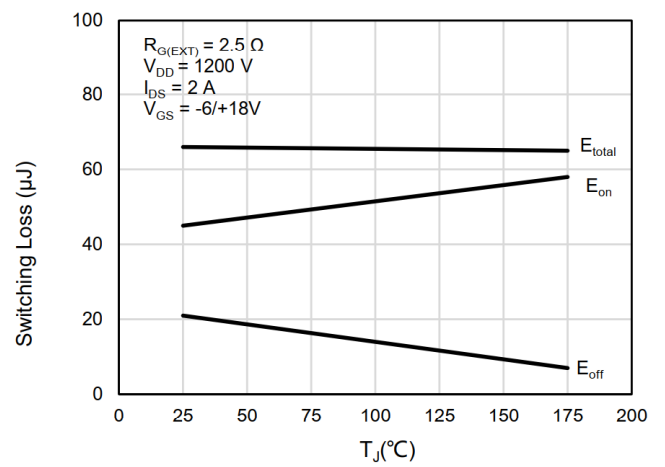


Figure 24: Clamped Inductive Switching Energy vs. T_J

Typical Performance (curves)

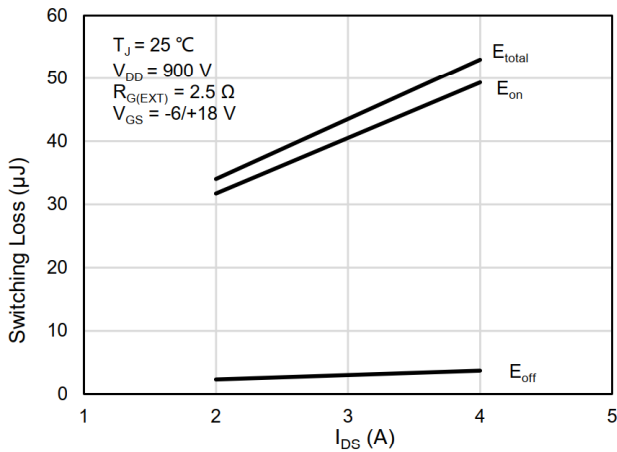


Figure 25: Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 600\text{ V}$)

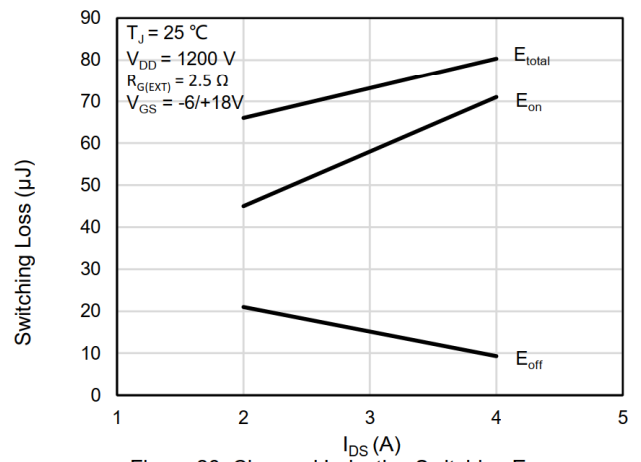


Figure 26: Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 1200\text{ V}$)

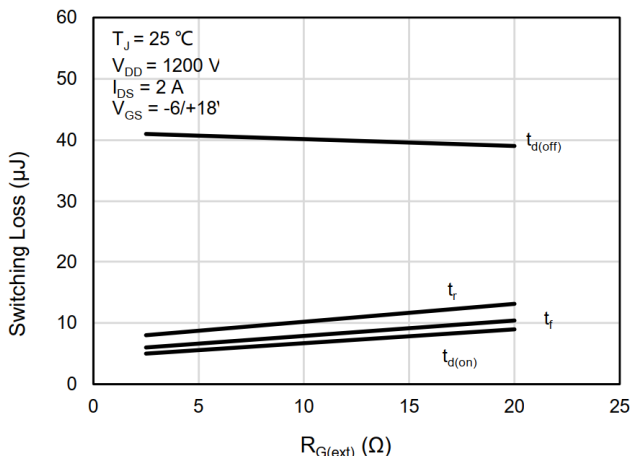


Figure 27: Switching Time vs. $R_{G(ext)}$

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